AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A method comprising:
placing a substrate with a ferroelectric polymer layer formed thereon in a chamber; and
sputtering a metal layer ~~at a reduced flux~~ on the ferroelectric polymer layer in the presence of a flux reducer.

2. (Currently Amended) The method of Claim 1, wherein ~~sputtering~~ the flux reducer comprises ~~sputtering in the presence of~~ a collimator.

3. (Currently Amended) The method of Claim 2, wherein sputtering ~~may be performed~~comprises sputtering at a pressure less than approximately 10 milliTorr.

4. (Currently Amended) The method of Claim ~~3~~2, wherein sputtering ~~may be performed~~comprises sputtering at a pressure equal to or less than approximately 2.5 milliTorr.

5. (Original) The method of Claim 1, wherein sputtering comprises:
forming a metal layer of at least one of TiN, TaN, TiNSi, and TaNSi.

6. (Original) The method of Claim 1, wherein sputtering comprises:
sputtering with an ion gun.

7. (Original) A method comprising:
placing a substrate with a ferroelectric polymer layer formed thereon in a chamber; and
forming an intermetallic layer between a metal layer and the ferroelectric polymer layer.

8. (Original) The method of Claim 7, wherein forming comprises:
sputtering with an ion gun.

9. (Original) The method of Claim 7, wherein forming comprises:
forming a layer of at least one of TiN, TaN, TiNSi, and TaNSi.

10. (Original) The method of Claim 7, further comprising:
amorphizing the intermetallic layer.

11. (Original) The method of Claim 10, wherein amorphizing comprises:
implanting ions within the intermetallic layer.

12. (Original) The method of Claim 11, wherein implanting comprises:
implanting at least one of Si ions, Ge ions, and any of the inert gas ions in the intermetallic layer.

13. (Original) The method of Claim 10, wherein amorphizing comprises:
forming the intermetallic layer with a technique that renders the intermetallic layer amorphous.

14. (Original) The method of Claim 13, wherein forming comprises:
forming the intermetallic layer with a chemical vapor deposition process.

15-24 (Canceled)

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